

PESD2CAN

CAN bus ESD protection diode Rev. 01 — 22 December 2006

Product data sheet

Product profile

1.1 General description

PESD2CAN in a small SOT23 Surface-Mounted Device (SMD) plastic package designed to protect two automotive Controller Area Network (CAN) bus lines from the damage caused by ElectroStatic Discharge (ESD) and other transients.

1.2 Features

- Due to the integrated diode structure only one small SOT23 package is needed to protect two CAN bus lines
- Max. peak pulse power: $P_{PP} = 230 \text{ W}$ at $t_p = 8/20 \text{ μs}$
- Low clamping voltage: V_{CL} = 41 V at I_{PP} = 5 A
- Ultra low leakage current: I_{RM} < 1 nA</p>
- ESD protection up to 30 kV
- IEC 61000-4-2, level 4 (ESD)
- IEC 61000-4-5 (surge); $I_{PP} = 5$ A at $t_p = 8/20$ μs
- Small SMD plastic package

1.3 Applications

- CAN bus protection
- Automotive applications

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode)					
V_{RWM}	reverse standoff voltage		-	-	24	V
C _d	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	25	30	pF



2 of 11

Pinning information 2.

Table 2 Pinning

Table 2.	i iiiiiiig		
Pin	Description	Simplified outline	Symbol
1	cathode 1		
2	cathode 2	3	1
3	common cathode	1 2	2 006aaa155

Ordering information 3.

Table 3. **Ordering information**

Type number	Package			
	Name	Description	Version	
PESD2CAN	-	plastic surface-mounted package; 3 leads	SOT23	

Marking

Table 4. **Marking codes**

Type number	Marking code ^[1]
PESD2CAN	6R*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

Limiting values 5.

Product data sheet

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
P _{PP}	peak pulse power	$t_p = 8/20 \ \mu s$	[1][2]	230	W
I _{PP}	peak pulse current	$t_p = 8/20 \ \mu s$	[1][2]	5	А
Per device					
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Non-repetitive current pulse 8/20 µs exponential decay waveform according to IEC 61000-4-5.

[2] Measured from pin 1 to 3 or 2 to 3.

Table 6. ESD maximum ratings

	•					
Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V _{ESD} electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	[1][2]	-	30	kV	
		machine model	[2]	-	400	V
		MIL-STD-883 (human body model)	[1][2]	-	16	kV

^[1] Device stressed with ten non-repetitive ESD pulses.

Table 7. ESD standards compliance

Standard	Conditions
Per diode	
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV

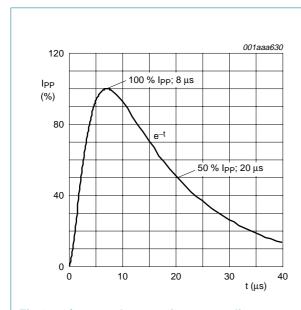


Fig 1. 8/20 μs pulse waveform according to IEC 61000-4-5

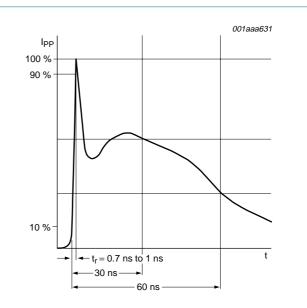


Fig 2. ESD pulse waveform according to IEC 61000-4-2

^[2] Measured from pin 1 to 3 or 2 to 3.

6. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

and	<u>'</u>						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diod	е						
V_{RWM}	reverse standoff voltage			-	-	24	V
I _{RM}	reverse leakage current	$V_{RWM} = 24 V$		-	< 1	10	nA
V_{BR}	breakdown voltage	$I_R = 1 \text{ mA}$		26.2	28	30.3	V
C_d	diode capacitance	$f = 1 MHz; V_R = 0 V$		-	25	30	pF
V_{CL}	clamping voltage	I _{PP} = 1 A	[1][2]	-	-	34	V
		I _{PP} = 5 A	[1][2]	-	-	41	V
r _{dif}	differential resistance	$I_R = 1 \text{ mA}$		-	-	300	Ω

- [1] Non-repetitive current pulse $8/20~\mu s$ exponential decay waveform according to IEC 61000-4-5.
- [2] Measured from pin 1 to 3 or 2 to 3.

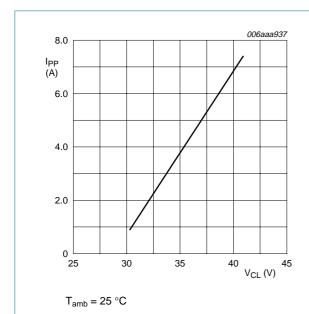


Fig 3. Peak pulse current as a function of clamping voltage; typical values

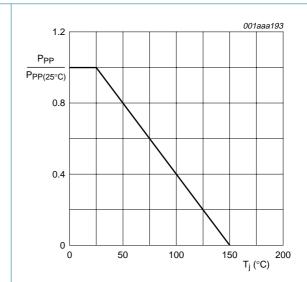
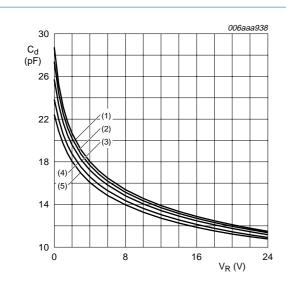


Fig 4. Relative variation of peak pulse power as a function of junction temperature; typical values



f = 1 MHz

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

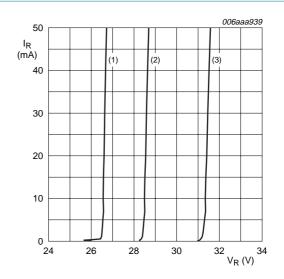
(2)
$$T_{amb} = 125 \, ^{\circ}C$$

(3)
$$T_{amb} = 85 \,^{\circ}C$$

(4)
$$T_{amb} = 25 \,^{\circ}C$$

(5)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Diode capacitance as a function of reverse voltage; typical values

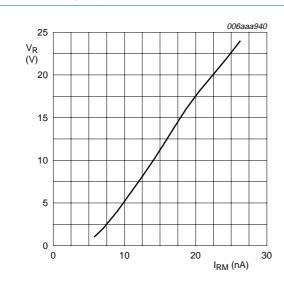


(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$





T_{amb} = 150 °C

 I_R is less than 1 nA at –55 °C and 25 °C.

Fig 7. Reverse voltage as a function of reverse leakage current; typical values

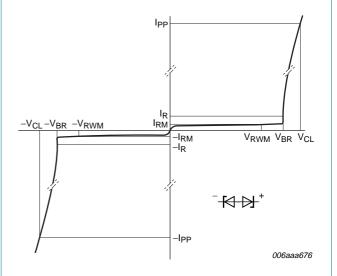


Fig 8. V-I characteristics for a bidirectional ESD protection diode

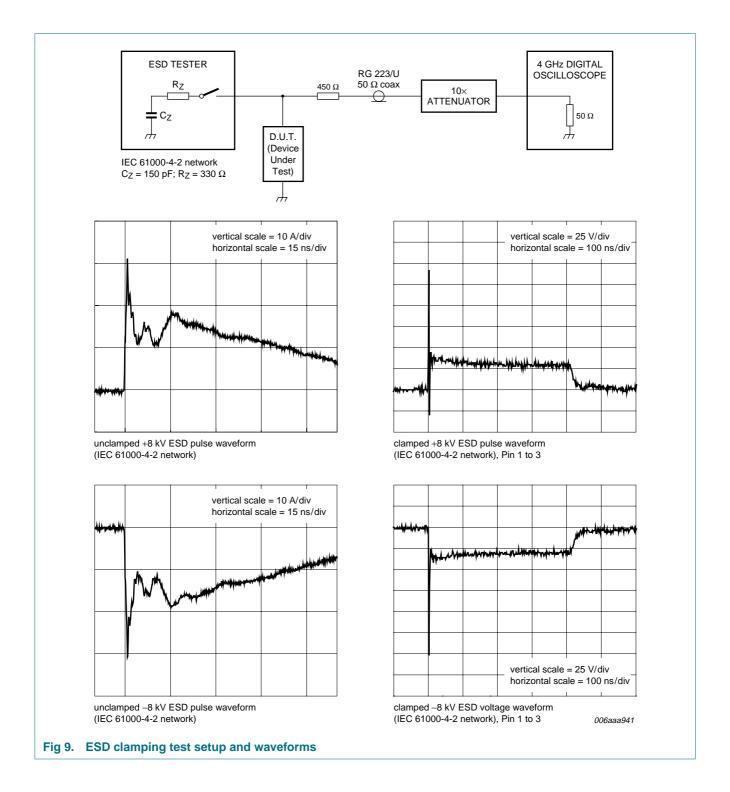
5 of 11

Product data sheet



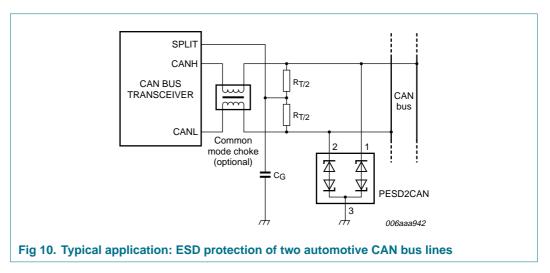
6 of 11

CAN bus **ESD** protection diode



7. Application information

The PESD2CAN is designed for the protection of two automotive CAN bus lines from the damage caused by ESD and surge pulses. The PESD2CAN can be used for both, high-speed CAN bus and fault-tolerant CAN bus protection. The PESD2CAN provides a surge capability of up to 230 W per line for an $8/20~\mu s$ waveform.

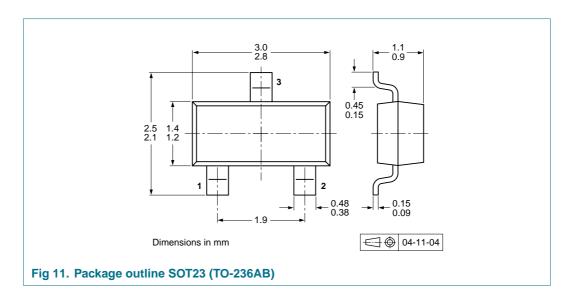


Circuit board layout and protection device placement:

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the PESD2CAN as close to the input terminal or connector as possible.
- 2. The path length between the PESD2CAN and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protection conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	antity
			3000	10000
PESD2CAN	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 12.



10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PESD2CAN_1	20061222	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

11.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

11.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

11.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

12. Contact information

For additional information, please visit: http://www.nxp.com

For sales office addresses, send an email to: salesaddresses@nxp.com



13. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications
1.4	Quick reference data
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values
6	Characteristics 4
7	Application information 7
8	Package outline 8
9	Packing information 8
10	Revision history 9
11	Legal information
11.1	Data sheet status
11.2	Definitions
11.3	Disclaimers
11.4	Trademarks10
12	Contact information
13	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

